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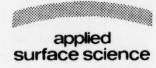
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- Ion beam synthesis of heteroepitaxial erbium silicide layers, M.F. Wu, A. Vantomme, H. Pattyn, G. Langouche and H. Bender
- Influence of growth conditions on the formation of deep photoluminescence bands in MBE-grown Si layers and SiGe/Si quantum structures, I.A. Buyanova,

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- X-ray standing wave study of Si/Ge superlattices, P. Castrucci, S. Lagomarsino, P. Calicchia and A. Cedola
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